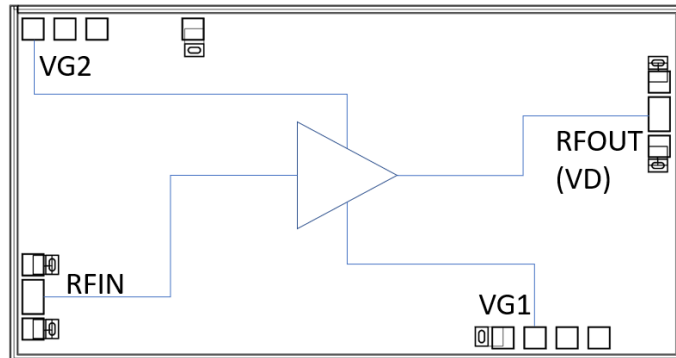


Features

- Frequency: DC-25GHz
- Small Signal Gain: 14dB
- Gain Flatness: $\leq \pm 1\text{dB}@DC-25\text{GHz}$
- Noise Figure: $\leq 3.7\text{ dB}@3-25\text{GHz}$
- P1dB: >15dBm, 16.5dBm at 10GHz
- Psat: >16.5dBm, 18dBm at 10GHz
- Power Supply: +8V/60mA
- Input/Output: 50 Ω
- Die Size: 3.12 x 1.63 x 0.1 mm

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Functional Block Diagram

Electrical Specifications

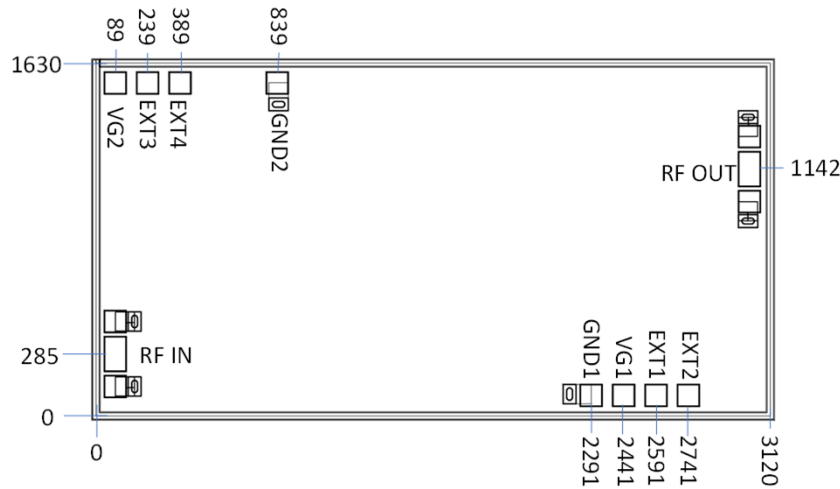
TA = +25°C, VD = +8V, VG1 = -0.4V, VG2 = 3.6V, ID = 60mA

Parameters	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency	DC-10			10-20			20-25			GHz
Small Signal Gain		14.0			13.6			13.5		dB
Gain Flatness		± 0.1			± 0.1			± 0.1		dB
Noise Figure		2.5			2.6			3.3		dB
Output 1dB Compression (P1dB)		16			15.5			15.0		dBm
Saturated Output Power (Psat)		17.5			17			16.6		dBm
Input Return Loss		25			22			20		dB
Output Return Loss		25			17			15		dB

* Adjust VG1, VG2 slightly to obtain device current of 60mA.



Outline Drawing:
All Dimensions in μm

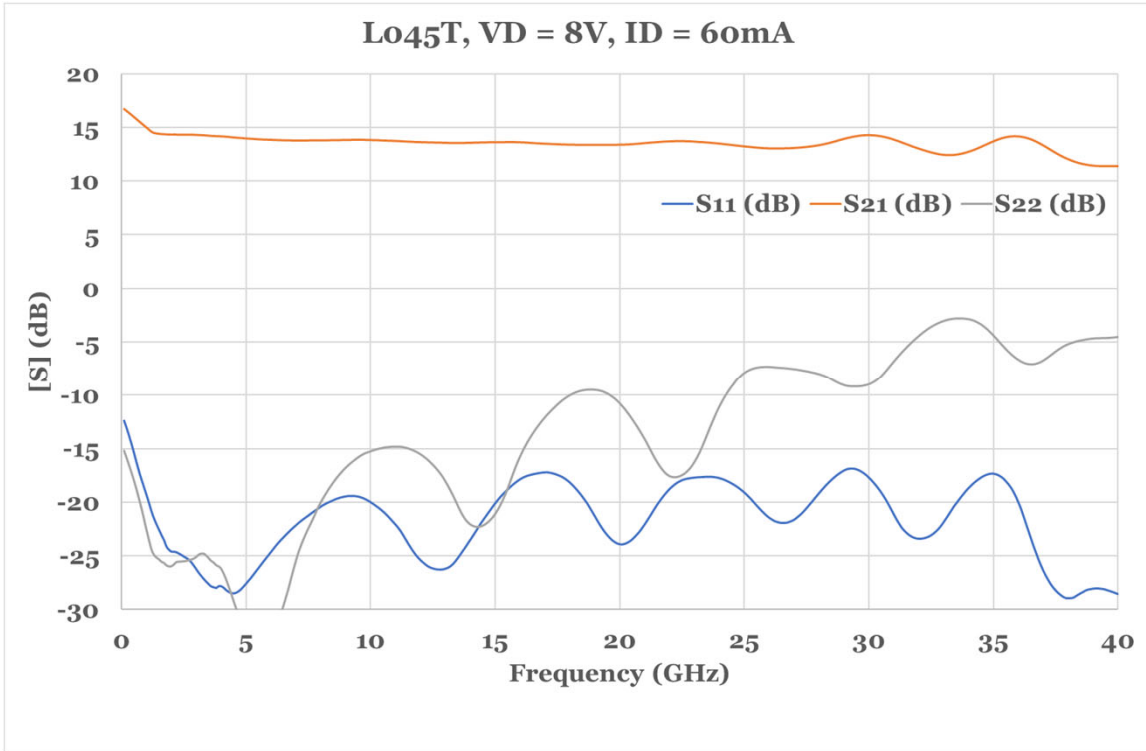


Pad Description

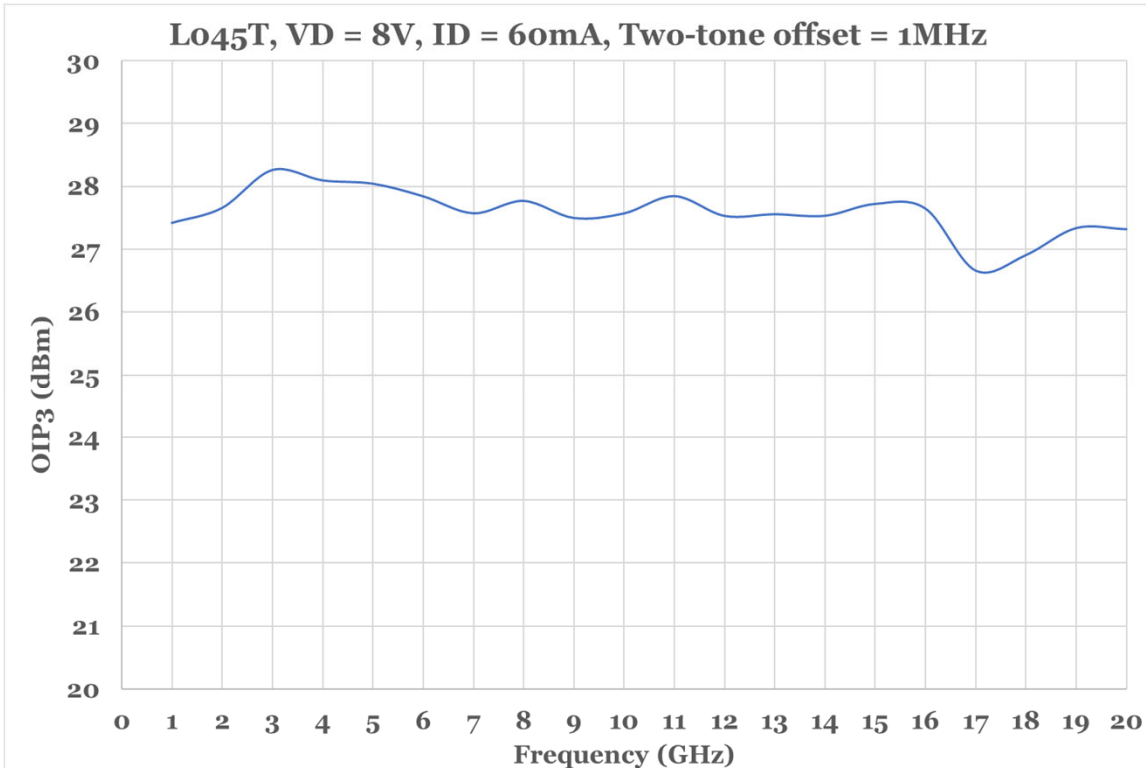
No	Function	Description
1	RF IN	Signal input terminal, connected to 50Ω circuit; blocking capacitor required.
2	RF OUT	Signal output terminal, connected to 50Ω circuit; blocking capacitor required; external DC biasing network required; drain current provided.
3	VG1	Amplifier 1 st gate bias; connect to external 1000pF and 0.1uF bypass capacitors.
4	VG2	Amplifier 2 nd gate bias; connect to external 1000pF and 0.1uF bypass capacitors.
5	EXT1	External bypass pad; connect to external 0.47uF bypass capacitor.
6	EXT2	External bypass pad; connect to external 1000pF bypass capacitor.
7	EXT3	External bypass pad; connect to external 1000pF bypass capacitor.
8	EXT4	External bypass pad; connect to external 0.47uF bypass capacitor.
9	GND1	Ground pad.
10	GND2	Ground pad.



Measurement Plots: S-parameters

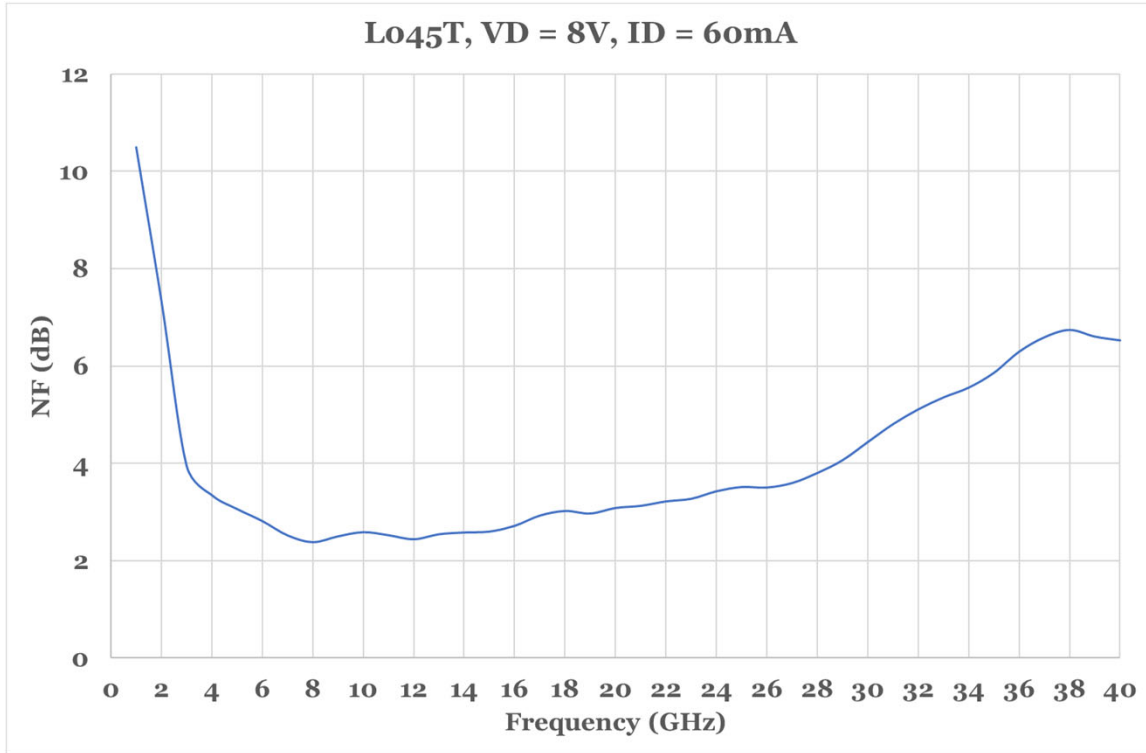


Measurement Plots: P1dB

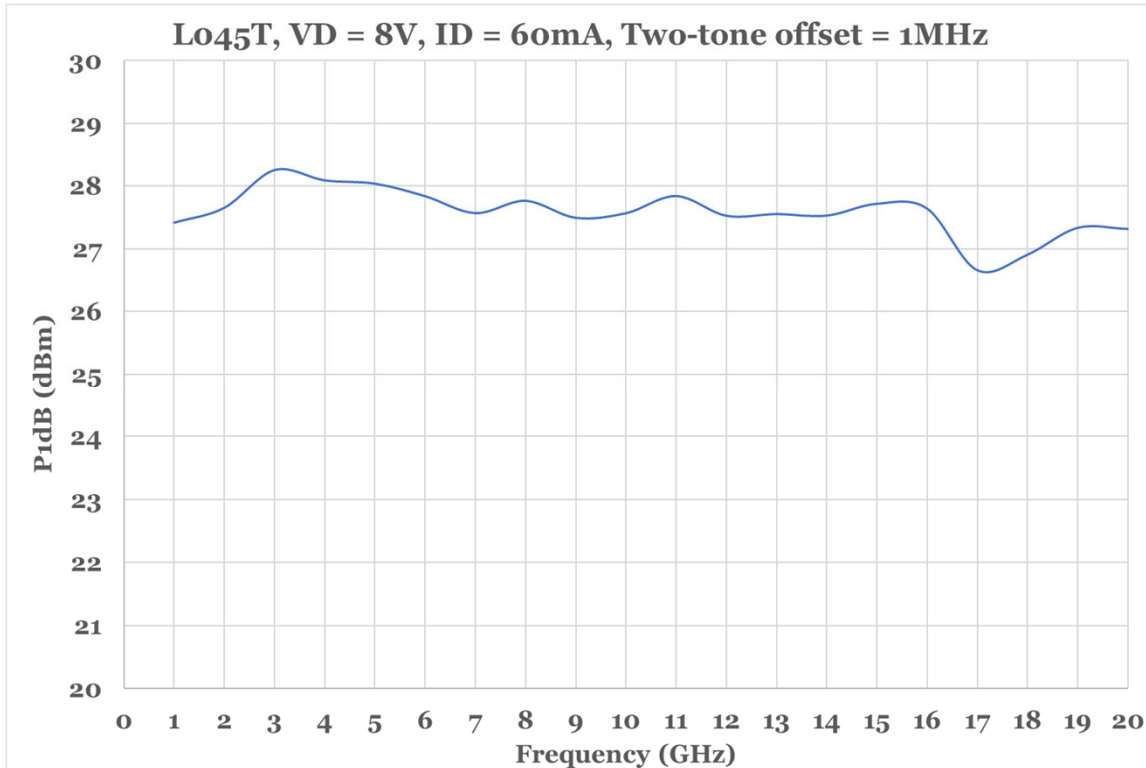




Measurement Plots: Noise Figure

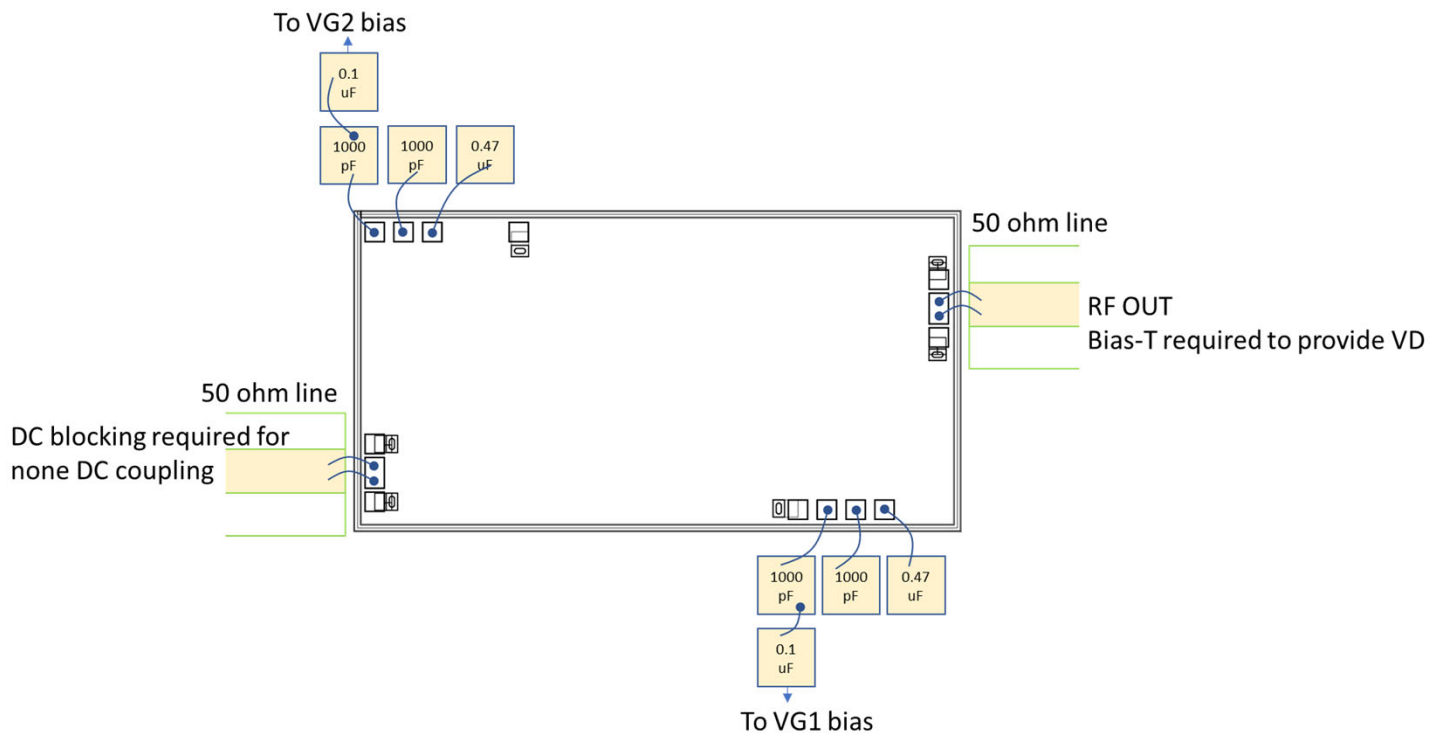


Measurement Plots: OIP3





Assembly Drawing



Notes:

1. Die thickness: 100um
2. DC bond pad is 100 x 100 μm^2
3. RF IN/OUT bond pad is 100 x 160 μm^2
4. Bond pad metalization: Gold
5. Backside metalization: Gold
6. Backside of the die (GND)

Maximum Ratings:

1. Maximum drain voltage: +10V
2. Maximum gate bias: -3V
3. Maximum input power: +20dBm
4. Operating temperature: -55°C to +85°C
5. Storage temperature: -65°C to +150°C